

# NTMS5835NL

## Power MOSFET

40 V, 12 A, 10 mΩ

### Features

- Low  $R_{DS(on)}$
- Low Capacitance
- Optimized Gate Charge
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	40	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current $R_{\theta JA}$ (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$ 9.2 A
		$T_A = 70^\circ\text{C}$	7.4
Power Dissipation $R_{\theta JA}$ (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$ 1.5 W
		$T_A = 70^\circ\text{C}$	1.0
Continuous Drain Current $R_{\theta JA}$ (Note 1)	$t \leq 10$ s	$T_A = 25^\circ\text{C}$	$I_D$ 12 A
		$T_A = 70^\circ\text{C}$	9.6
Power Dissipation $R_{\theta JA}$ (Note 1)	$t \leq 10$ s	$T_A = 25^\circ\text{C}$	$P_D$ 2.6 W
		$T_A = 70^\circ\text{C}$	1.6
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	$I_{DM}$ 48	A
Operating Junction and Storage Temperature	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode)	$I_S$	20	A
Single Pulse Drain-to-Source Avalanche Energy ( $V_{DD} = 40$ V, $V_{GS} = 10$ V, $L = 0.1$ mH)	EAS	69	mJ
	IAS	37	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Ambient Steady State (Note 1)	$R_{\theta JA}$	82	$^\circ\text{C/W}$
Junction-to-Ambient - $t \leq 10$ s (Note 1)	$R_{\theta JA}$	49	
Junction-to-Foot (Drain) (Note 1)	$R_{\theta JF}$	21	
Junction-to-Ambient Steady State (Note 2)	$R_{\theta JA}$	121	

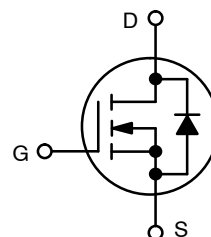
1. Surface-mounted on FR4 board using 1 sq-in pad (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using 0.155 in sq (100mm<sup>2</sup>) pad size.



ON Semiconductor®

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$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	10 mΩ @ 10 V	12 A
	14 mΩ @ 4.5 V	

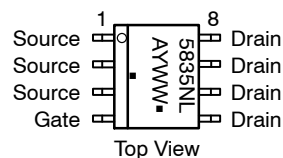


N-CHANNEL MOSFET



SO-8  
CASE 751  
STYLE 12

### MARKING DIAGRAM/ PIN ASSIGNMENT



A = Assembly Location  
Y = Year  
WW = Work Week  
■ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NTMS5835NLR2G	SO-8 (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			16		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$	$T_J = 25^\circ\text{C}$		1	$\mu\text{A}$
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA

### ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.0	1.85	3.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			7.0		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		8.2	10	$\text{m}\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$		10.3	14	
Forward Transconductance	$g_{FS}$	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$		10		S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 20\text{ V}$		2115		$\text{pF}$
Output Capacitance	$C_{OSS}$			315		
Reverse Transfer Capacitance	$C_{RSS}$			220		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}; I_D = 10\text{ A}$		40	50	$\text{nC}$
				20	23	
Threshold Gate Charge	$Q_{G(TH)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 20\text{ V}; I_D = 10\text{ A}$		2.0		
Gate-to-Source Charge	$Q_{GS}$			7.0		
Gate-to-Drain Charge	$Q_{GD}$			9.5		
Plateau Voltage	$V_{GP}$			3.3		V
Gate Resistance	$R_G$			1.2		$\Omega$

### SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 20\text{ V}, I_D = 10\text{ A}, R_G = 2.5\text{ }\Omega$		15		$\text{ns}$
Rise Time	$t_r$			45		
Turn-Off Delay Time	$t_{d(OFF)}$			22		
Fall Time	$t_f$			9.0		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V},$ $I_S = 10\text{ A}$	$T_J = 25^{\circ}\text{C}$		0.9	1.2	V
			$T_J = 125^{\circ}\text{C}$		0.785		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 10\text{ A}$			26		ns
Charge Time	$t_a$				13		
Discharge Time	$t_b$				13		
Reverse Recovery Charge	$Q_{RR}$				17		nC

3. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

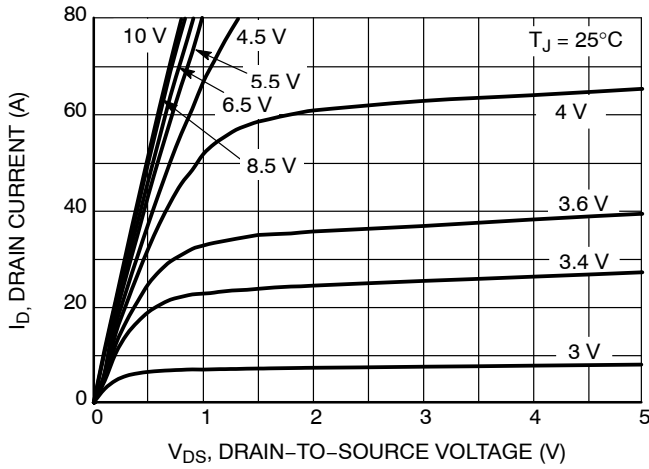


Figure 1. On-Region Characteristics

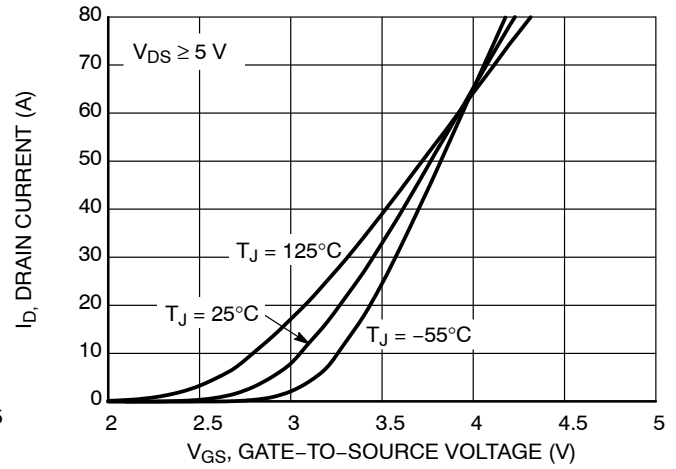


Figure 2. Transfer Characteristics

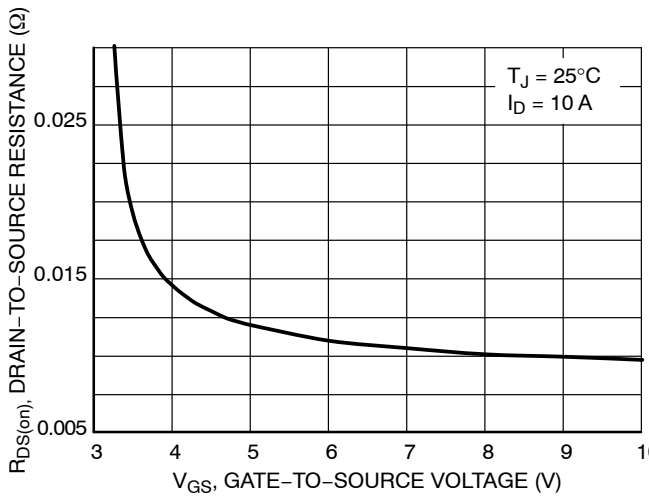


Figure 3. On-Resistance vs. Gate-to-Source Voltage

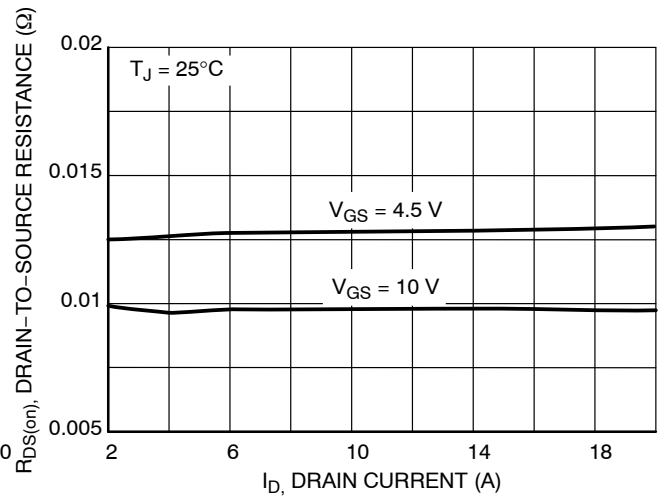


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

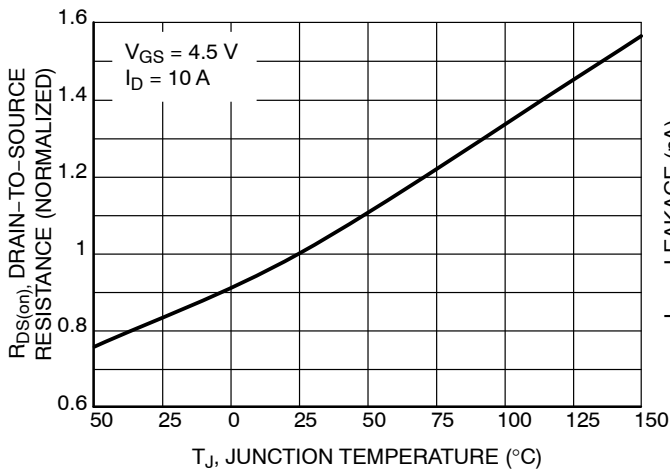


Figure 5. On-Resistance Variation with Temperature

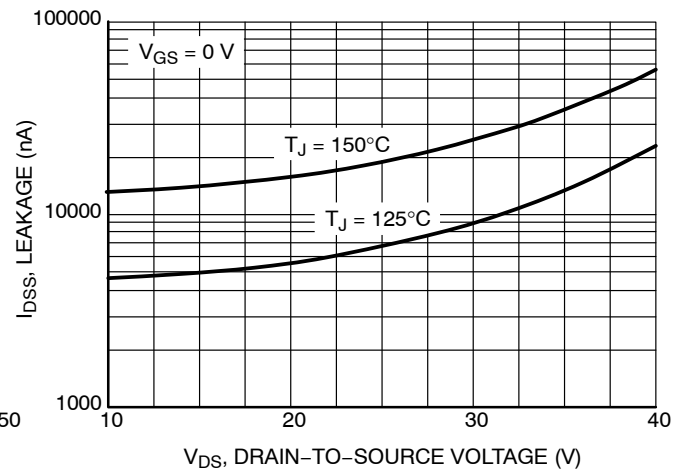


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

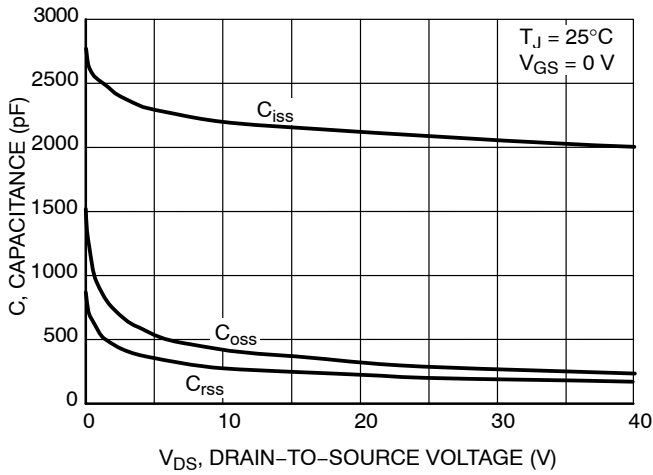


Figure 7. Capacitance Variation

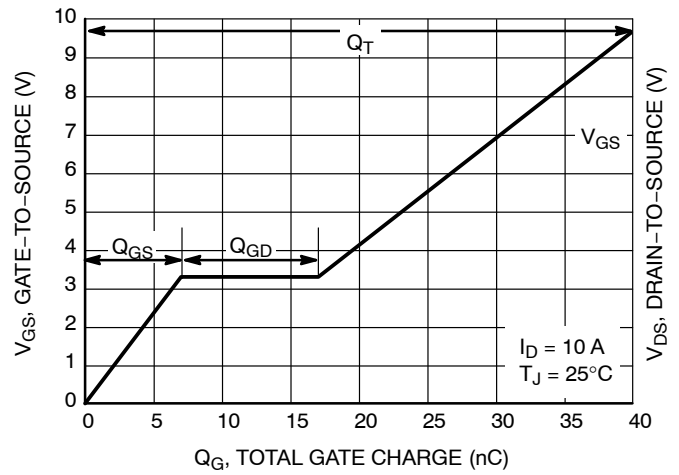


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

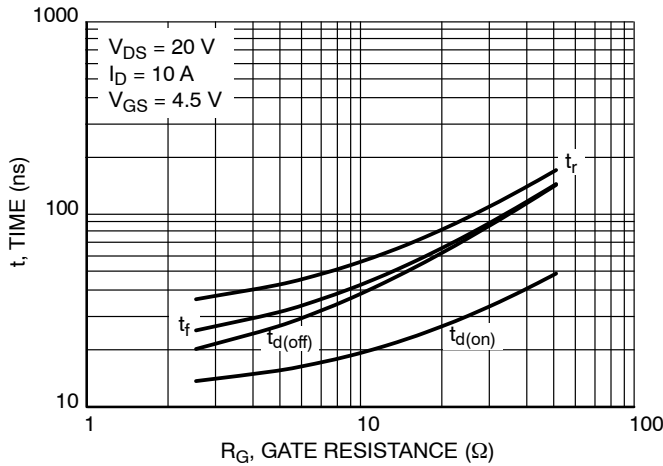


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

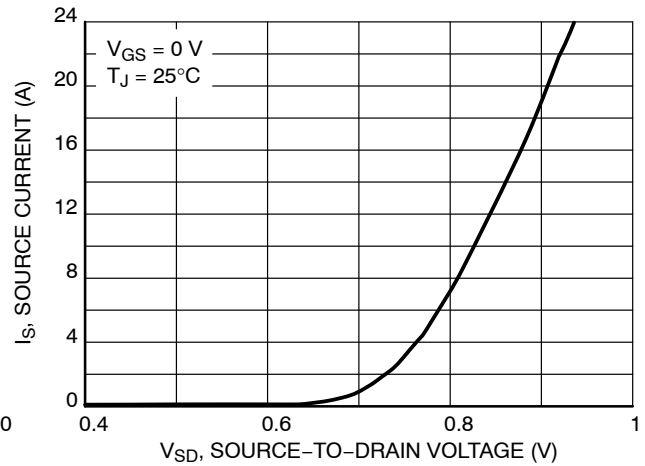


Figure 10. Diode Forward Voltage vs. Current

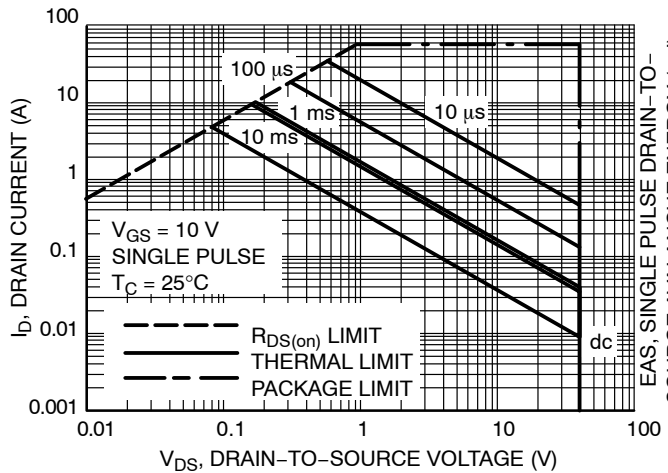


Figure 11. Maximum Rated Forward Biased Safe Operating Area

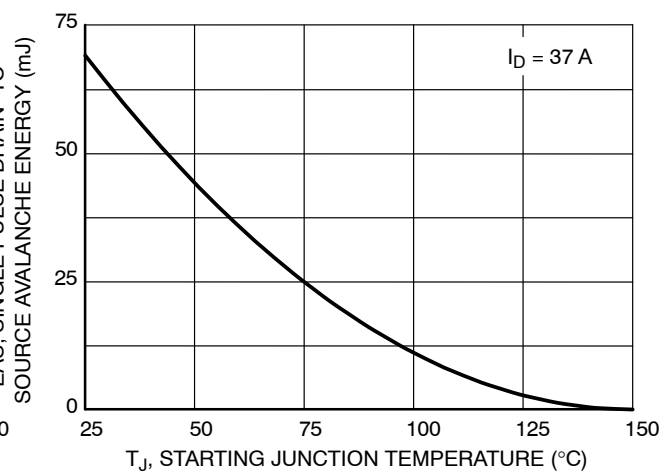


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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## TYPICAL PERFORMANCE CURVES

